AON7407
20V P-Channel MOSFET

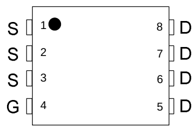
General Description

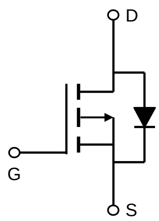
The AON7407 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

Features

V_{DS}	-20V
I_D (at V_{GS}=-4.5V)	-40A
$R_{DS(ON)}$ (at V_{GS} =-4.5V)	< 9.5mΩ
$R_{DS(ON)}$ (at V_{GS} =-2.5V)	< 12.5mΩ
$R_{DS(ON)}$ (at V_{GS} =-1.8V)	< 18mΩ

Top View





Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current [G]	T_C=25℃	I_D	-40	A
	T_C=100℃		-29	
Pulsed Drain Current [C]		I_{DM}	-100	
Continuous Drain Current	T_A=25℃	I_{DSM}	-14.5	A
	T_A=70℃		-11.5	
Avalanche Current [C]		I_{AS}, I_{AR}	-40	A
Avalanche energy L=0.1mH [C]		E_{AS}, E_{AR}	80	mJ
Power Dissipation [B]	T_C=25℃	P_D	29	W
	T_C=100℃		12	
Power Dissipation [A]	T_A=25℃	P_{DSM}	3.1	W
	T_A=70℃		2	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	℃

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	30	40	℃/W
Maximum Junction-to-Ambient [A D]	Steady-State		60	75	℃/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	3.5	4.2	℃/W

Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V		-20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-20V, V_{GS}=0V				-1	µA
			T_J=55℃			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±8V				±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250µA		-0.3	-0.55	-0.9	V
$I_{D(ON)}$	On state drain current	V_{GS}=-4.5V, V_{DS}=-5V		-100			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-4.5V, I_D=-14A			7.6	9.5	mΩ
			T_J=125℃		10.5	13.5	
		V_{GS}=-2.5V, I_D=-13A			9.3	12.5	mΩ
		V_{GS}=-1.8V, I_D=-11A			11.4	18	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-14A			72		S
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V			-0.52	-1	V
I_S	Maximum Body-Diode Continuous Current					-35	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-10V, f=1MHz		2795	3495	4195	pF
C_{oss}	Output Capacitance			365	528	690	pF
C_{rss}	Reverse Transfer Capacitance			255	425	595	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz			2.8	5.6	Ω
SWITCHING PARAMETERS							
Q_g	Total Gate Charge	V_{GS}=-4.5V, V_{DS}=-10V, I_D=-14A		35	44	53	nC
Q_{gs}	Gate Source Charge				9		nC
Q_{gd}	Gate Drain Charge				11		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-4.5V, V_{DS}=-10V, R_L=0.75Ω, R_{GEN}=3Ω			18		ns
t_r	Turn-On Rise Time				32		ns
$t_{D(off)}$	Turn-Off DelayTime				136		ns
t_f	Turn-Off Fall Time				59		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-14A, dI/dt=500A/µs		26	33	40	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-14A, dI/dt=500A/µs		80	100	120	nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25℃. The Power dissipation P_{DSM} is based on R $_{\theta JA}$ t ≤ 10s value and the maximum allowed junction temperature of 150℃. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150℃, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150℃. Ratings are based on low frequency and duty cycles to keep initial T_J =25℃.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150℃. The SOA curve provides a single pulse ratin g.
G. The maximum current rating is package limited.
H. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25℃.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

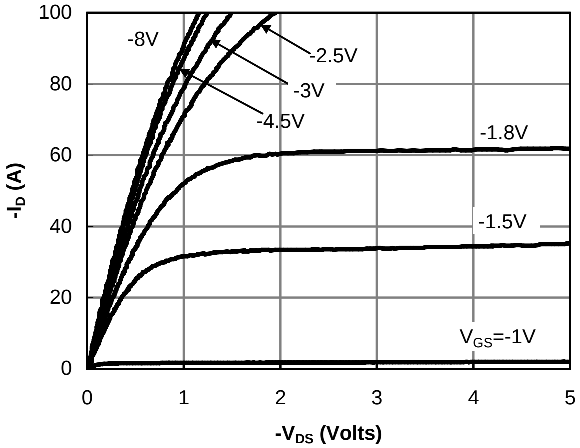


Fig 1: On-Region Characteristics (Note E)

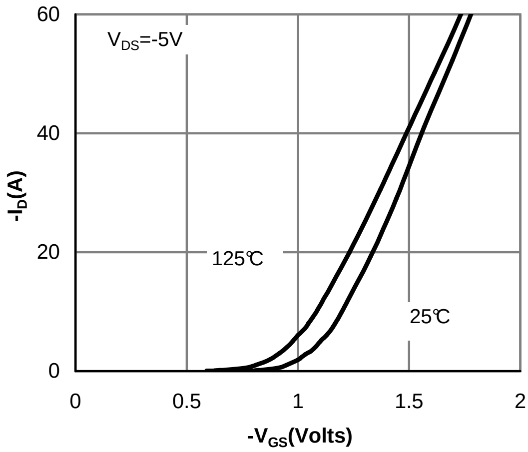


Figure 2: Transfer Characteristics (Note E)

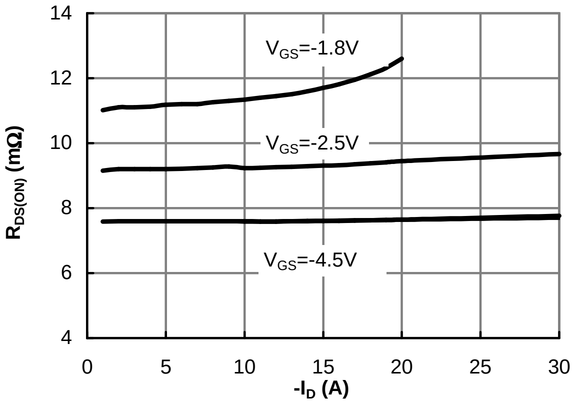


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

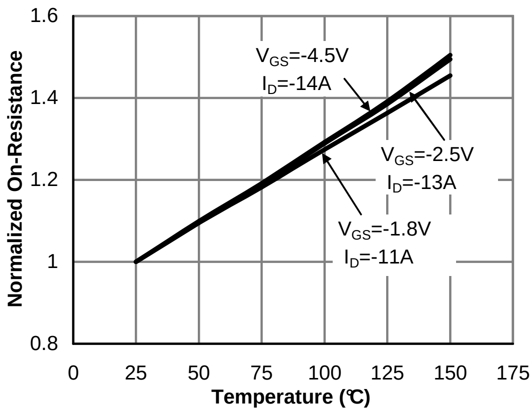


Figure 4: On-Resistance vs. Junction Temperature (Note E)

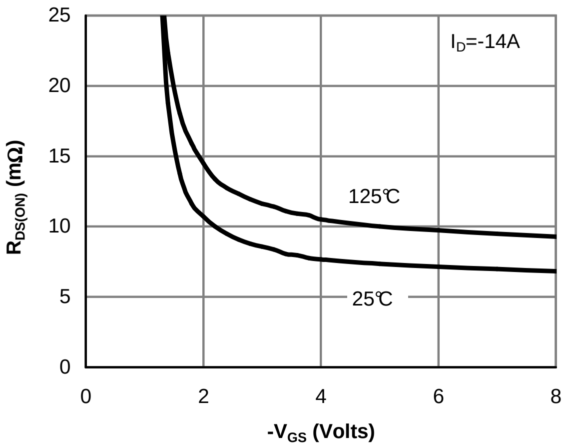


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

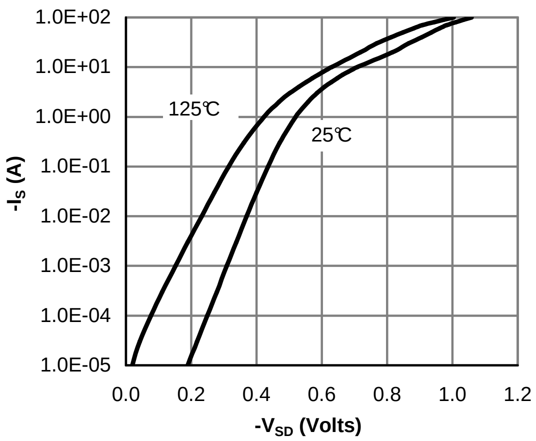


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

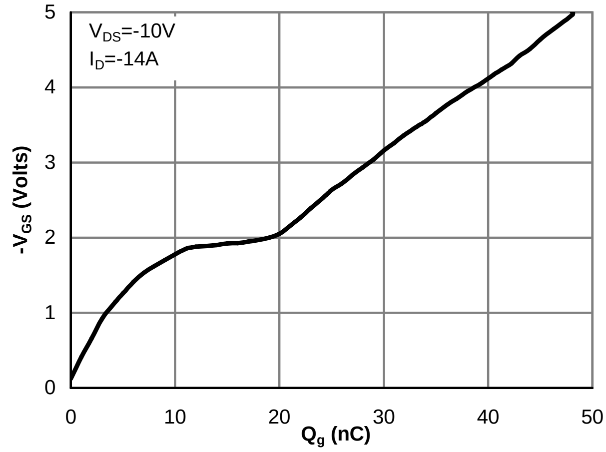


Figure 7: Gate-Charge Characteristics

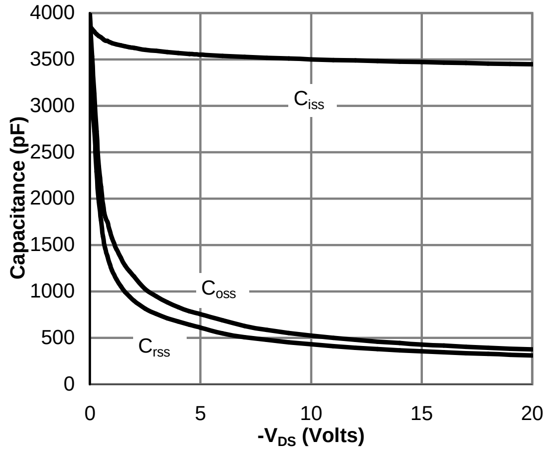


Figure 8: Capacitance Characteristics

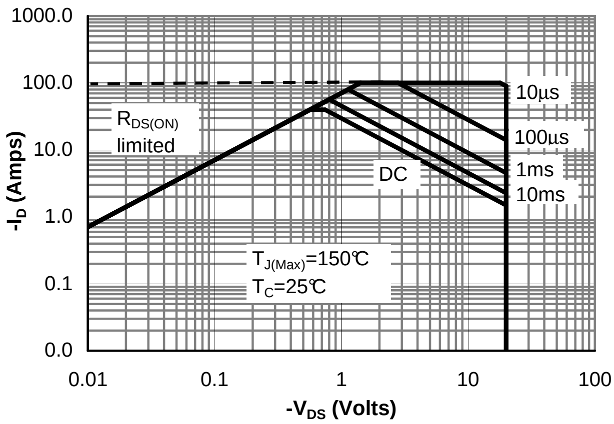


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

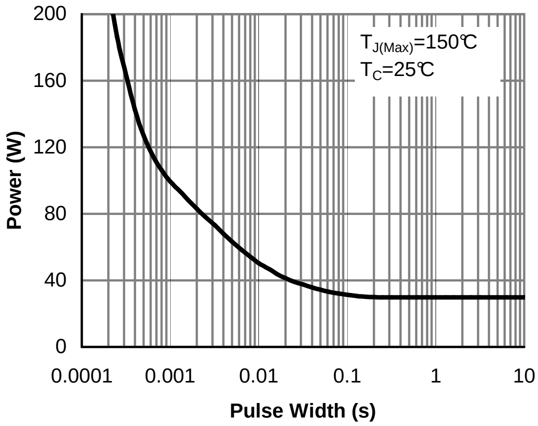


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

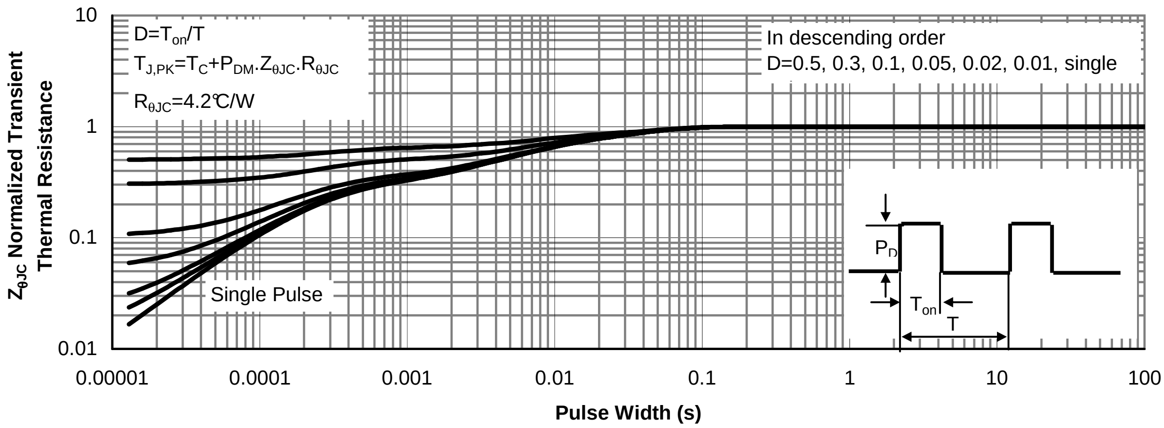


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

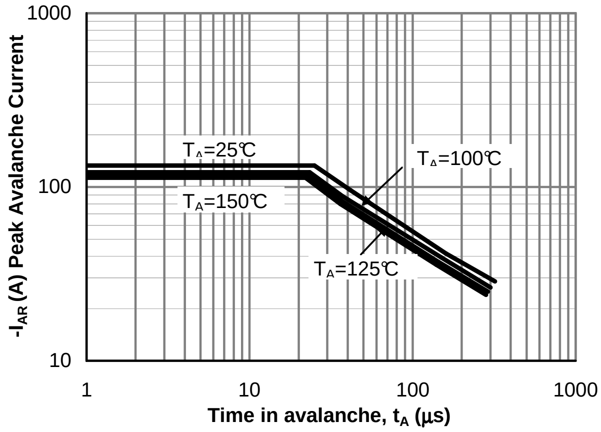


Figure 12: Single Pulse Avalanche capability (Note C)

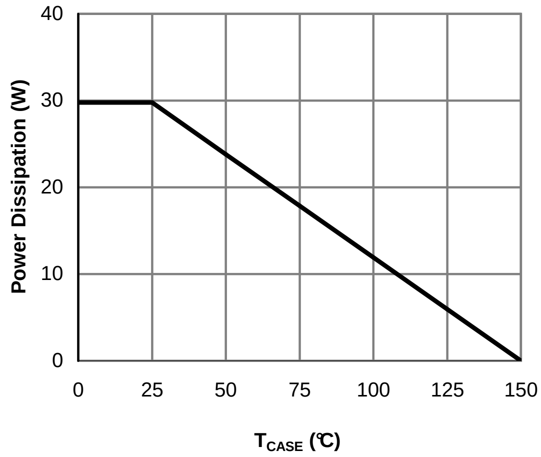


Figure 13: Power De-rating (Note F)

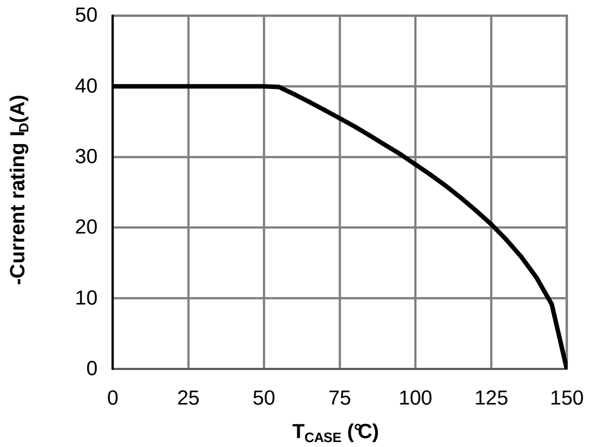


Figure 14: Current De-rating (Note F)

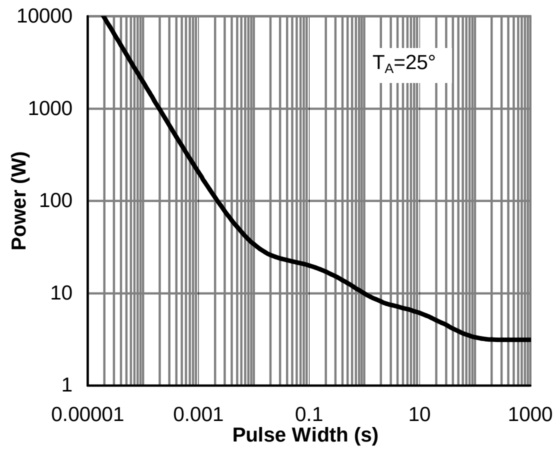


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

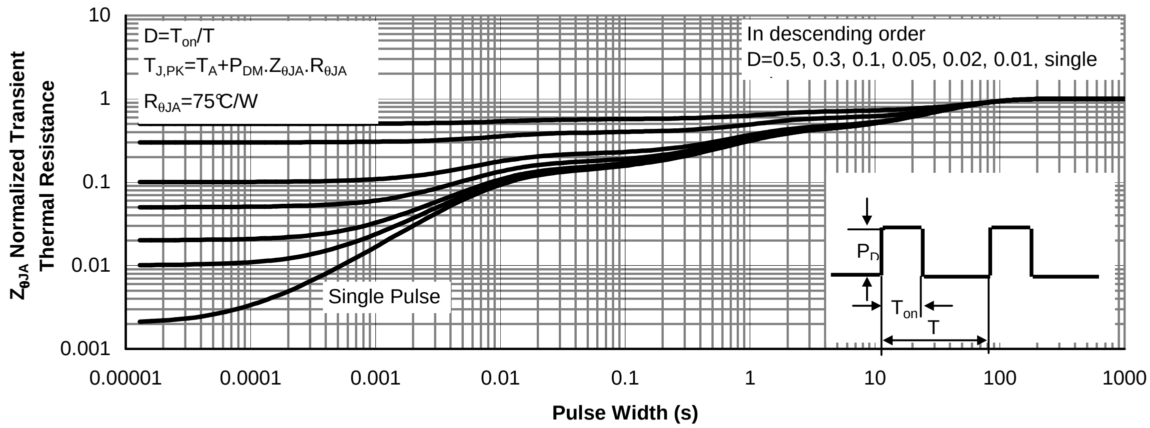
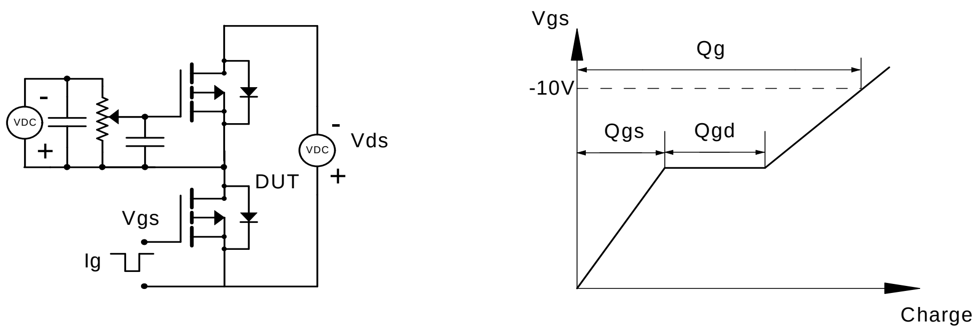
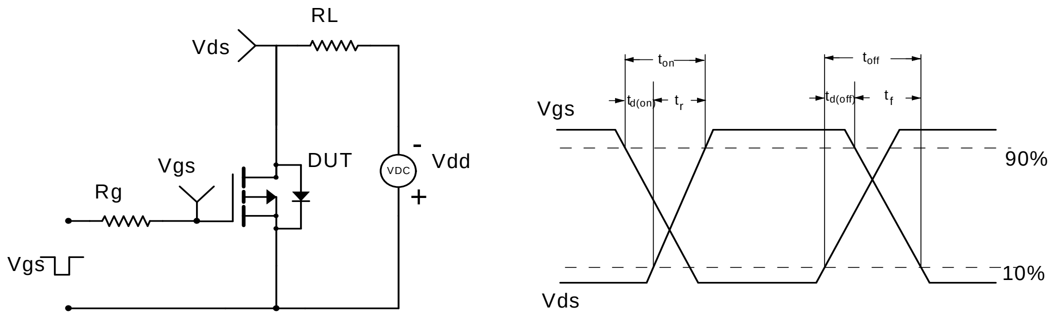


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

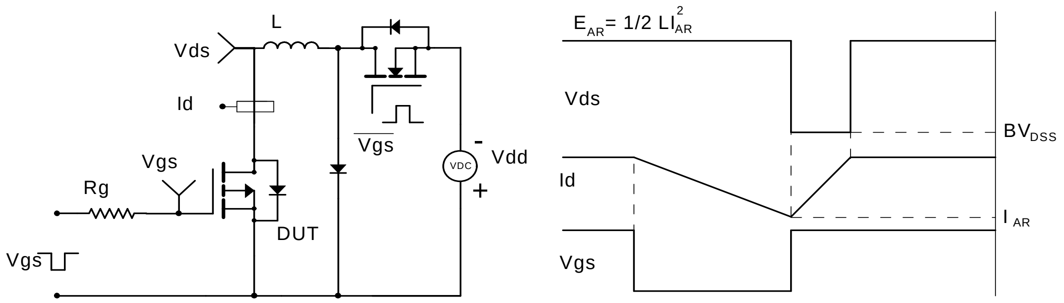
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms